

TS1998-850/852B

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ORIGINAL FILED

29 August 2002

To: Commissioner of Patents and Trademarks  
Washington, DC 20231

ATTN: Group Art Unit: 2814 PIZARRO, MARCOS D.

From: George O. Saile, Reg. No. 19,572  
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Serial No. 09/932,680  
C.J. LIN, et al.,

08/20/2001

FLASH MEMORY WITH OPTIMUM IMPLANT  
ANGLE FOR DOUBLE DRAIN DOPING

Group Art Unit: 2814 PIZARRO, M.D.

### RESPONSE PATENT OFFICE ACTION

Dear Sir:

In response to the Office Action dated 06/03/02, please amend the above-identified application for patent as follows:

### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patent and Trademarks, Washington, DC 20231, on, Sept. 3, 2002

Stephen B. Ackerman, Reg. No: 37,761

Signature



Date September 3, 2002

TS1998-850/852B

AMENDMENT

The Commissioner is hereby authorized to charge payment of any additional fees involved with added Claims and the like to Deposit Account No. 19-0033.

IN THE SPECIFICATION

Please replace the title of the invention with the following rewritten title:

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A1 FLASH MEMORY WITH OPTIMUM IMPLANT ANGLE FOR DOUBLE DRAIN  
DOPING

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IN THE CLAIMS

Please amend the claims as follows:

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A2 29. A stacked gate having a doubly diffused drain (DDD)  
SUB comprising:  
B1